

Title (en)
FERROELECTRIC MEMORY DEVICE

Title (de)
FERROELEKTRISCHE SPEICHERVORRICHTUNG

Title (fr)
DISPOSITIF DE MEMOIRE FERROELECTRIQUE

Publication
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Application
EP 14725226 A 20140416

Priority
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Abstract (en)
[origin: WO2014170606A1] The invention relates to a ferroelectric memory device comprising at least one layer comprising a ferroelectric polymer, and at least two electrodes either side thereof, the ferroelectric polymer being of general formula P(VDF-X-Y), wherein VDF is vinylidene fluoride motifs, X is trifluoroethylene or tetrafluoroethylene motifs, and Y is motifs from a third monomer, the molar proportion of Y motifs in the polymer being less than or equal to 6.5%.

IPC 8 full level
H01L 21/28 (2006.01); **C08F 214/18** (2006.01); **G11C 11/22** (2006.01); **H01G 4/14** (2006.01); **H01L 21/336** (2006.01); **H01L 27/10** (2006.01); **H01L 27/28** (2006.01); **H01L 29/51** (2006.01); **H01L 29/66** (2006.01); **H01L 29/78** (2006.01); **H01L 29/861** (2006.01); **H01L 49/02** (2006.01); **H01L 51/00** (2006.01); **H01L 51/05** (2006.01)

CPC (source: EP US)
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C-Set (source: EP US)
1. **C08F 214/22** + **C08F 214/26**
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Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

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DOCDB simple family (publication)
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